

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

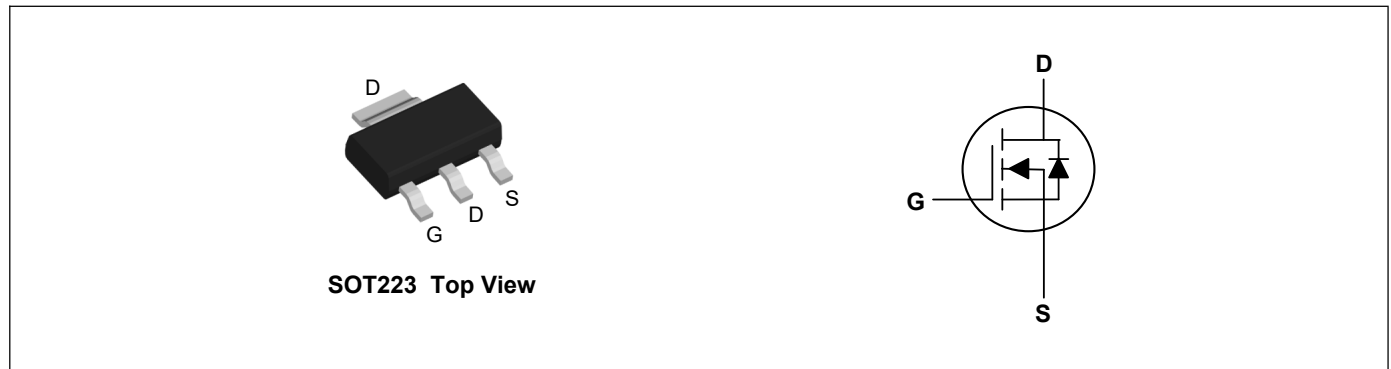
Product Summary



V_{DS}	100	V
I_D	6	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	47	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	50	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings ($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=25^{\circ}C$	6	A
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=70^{\circ}C$	4.7	A
Pulsed Drain Current ²	I_{DM}	24	A
Single Pulse Avalanche Energy ³	EAS	11.3	mJ
Avalanche Current	I_{AS}	15	A
Total Power Dissipation ⁴	$P_D@T_A=25^{\circ}C$	1.5	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	$R_{\theta JA}$	---	70	$^{\circ}C/W$
Thermal Resistance Junction-Ambient ¹ (Steady State)		---	35	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	---	---	V
BV _{DSS} Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =5A	---	---	47	mΩ
		V _{GS} =4.5V, I _D =5A	---	---	50	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.5	V
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)}		---	-5.52	---	mV/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =5A	---	6.2	---	S
Total Gate Charge	Q _g	V _{DS} =80V, V _{GS} =10V, I _D =5A	---	60	---	nC
Gate-Source Charge	Q _{gs}		---	9.2	---	
Gate-Drain Charge	Q _{gd}		---	9.9	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω, I _D =3A	---	10.8	---	ns
Rise Time	T _r		---	27	---	
Turn-Off Delay Time	T _{d(off)}		---	56	---	
Fall Time	T _f		---	24	---	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3848	---	pF
Output Capacitance	C _{oss}		---	137	---	
Reverse Transfer Capacitance	C _{rss}		---	82	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	6	A
Pulsed Source Current ^{2,5}	I _{SM}		---	---	24	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =5A, di/dt=100A/μs, T _J =25°C	---	25	---	nS
Reverse Recovery Charge	Q _{rr}		---	29	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

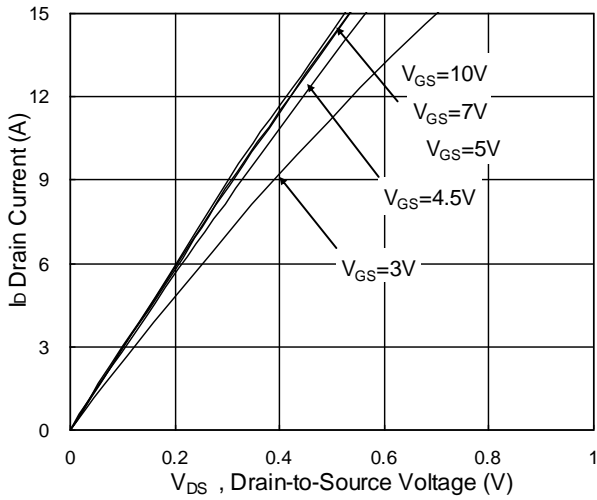


Fig.1 Typical Output Characteristics

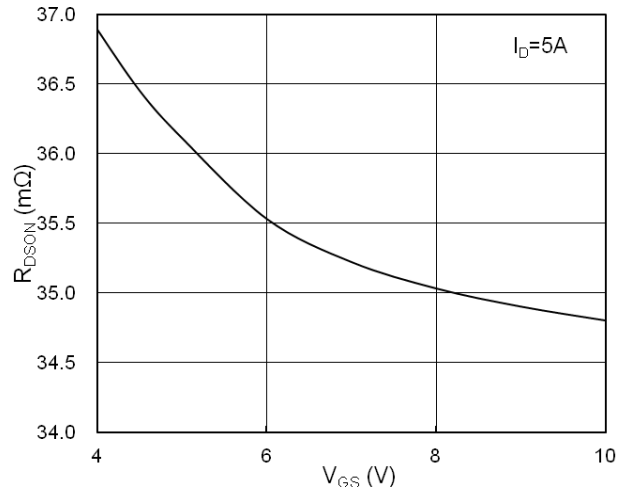


Fig.2 On-Resistance vs. Gate-Source

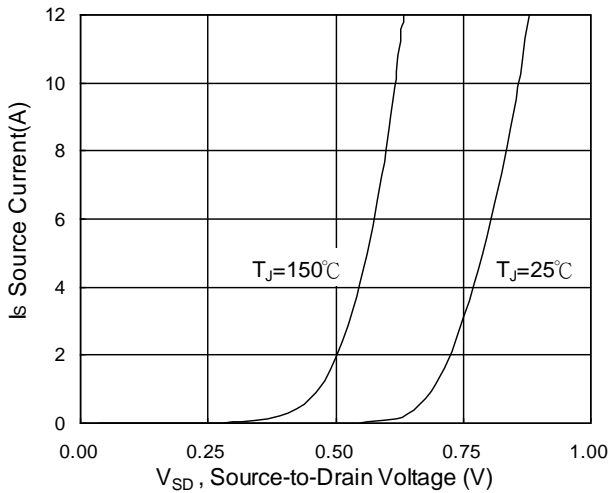


Fig.3 Forward Characteristics Of Reverse

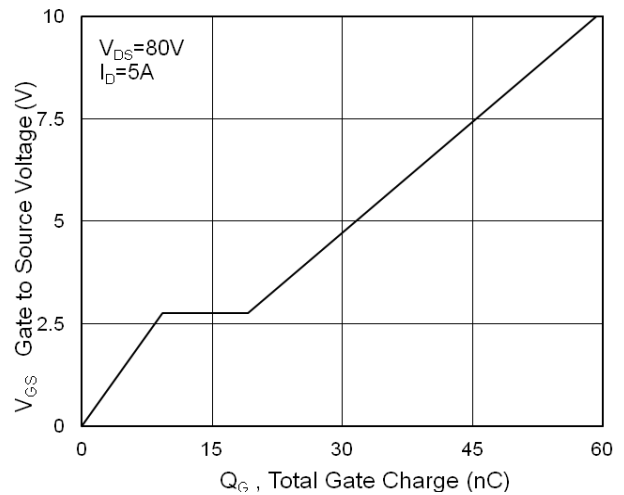


Fig.4 Gate-Charge Characteristics

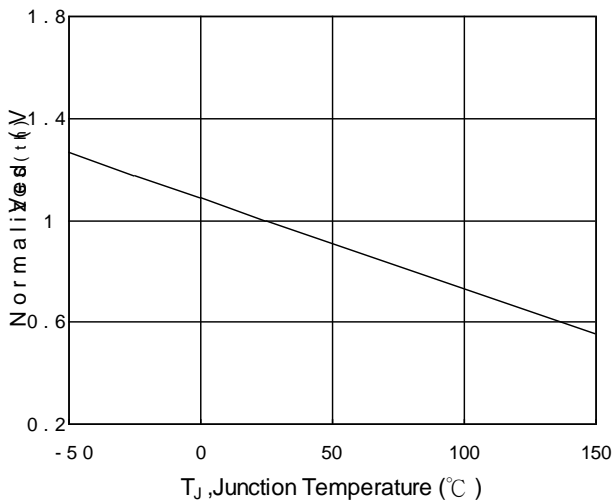


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

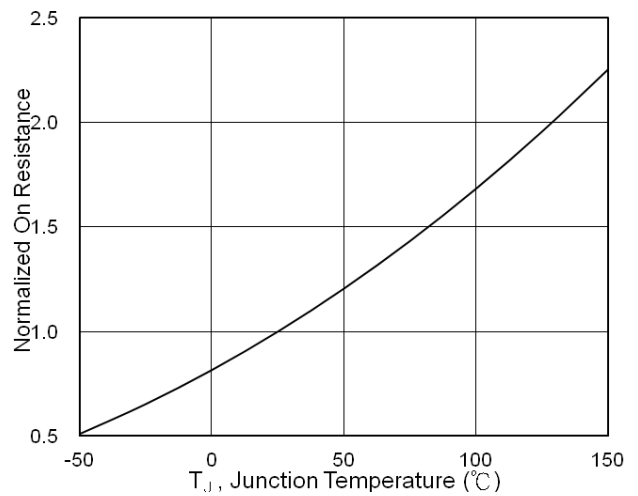


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

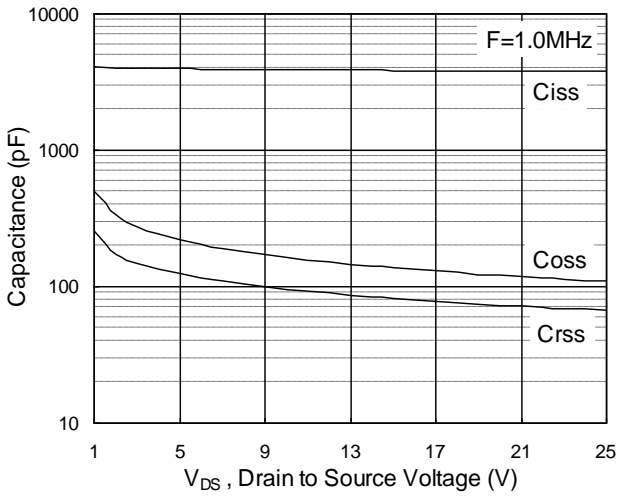


Fig.7 Capacitance

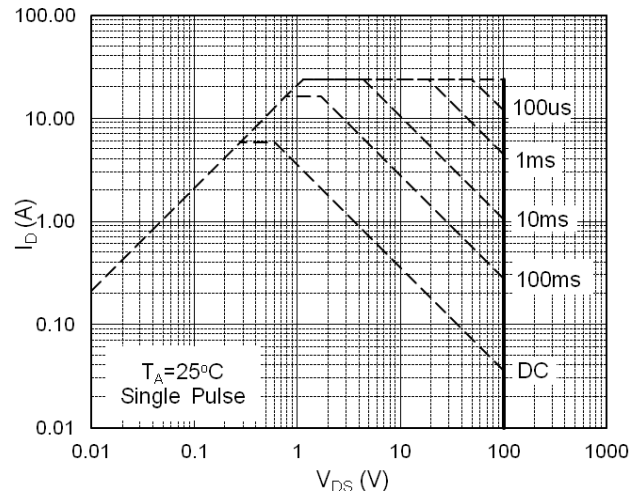


Fig.8 Safe Operating Area

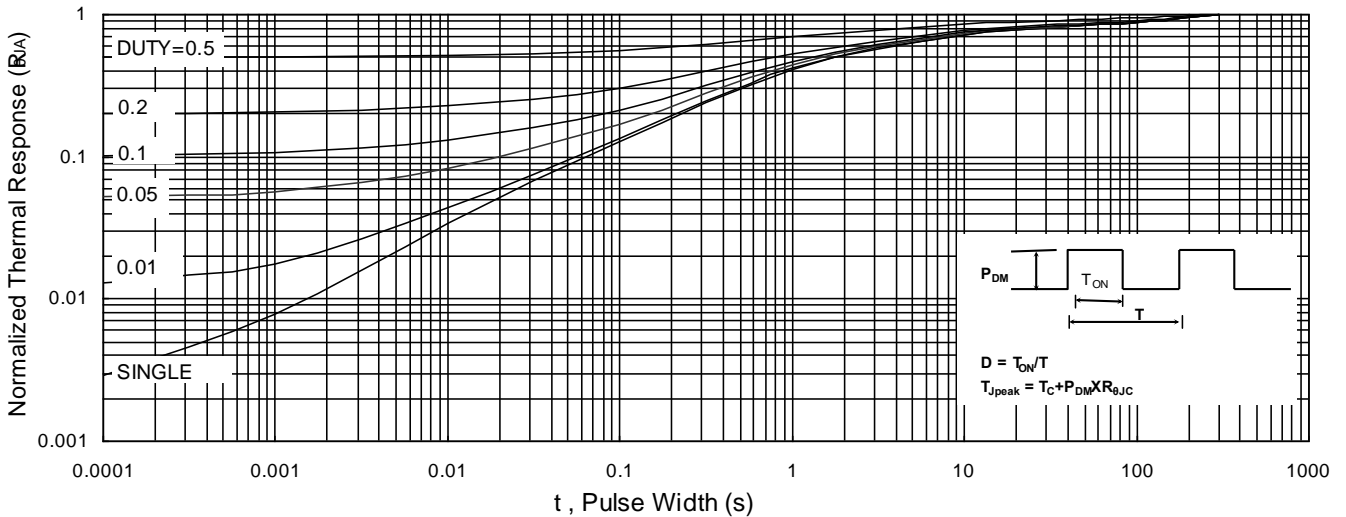


Fig.9 Normalized Maximum Transient Thermal Impedance

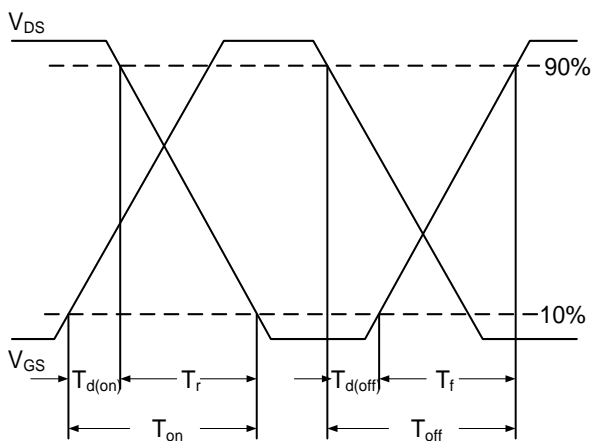


Fig.10 Switching Time Waveform

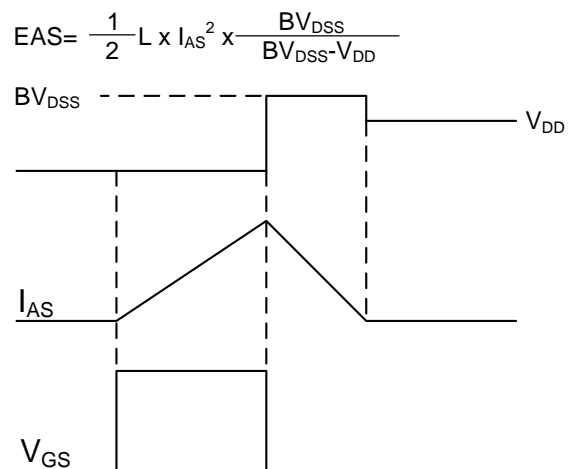
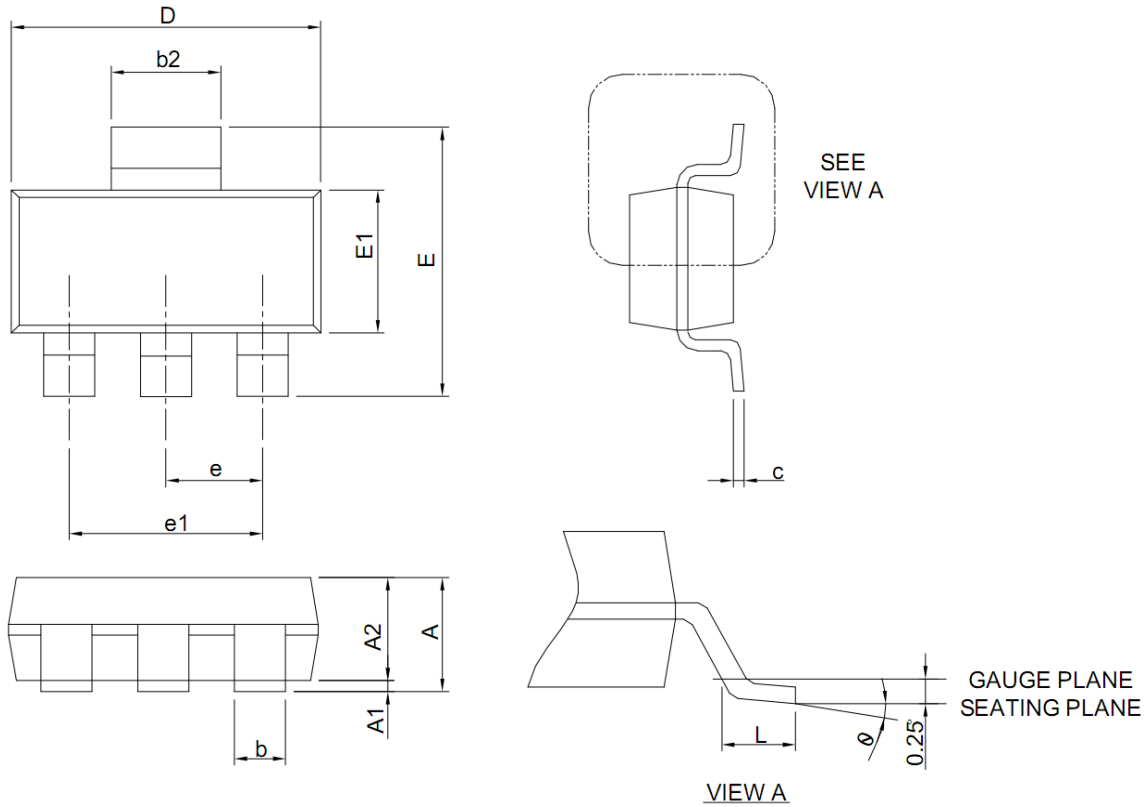


Fig.11 Unclamped Inductive Switching Waveform

SOT223 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	1.50	1.65	1.80	A1	0.02	0.06	0.10
A2	1.50	1.60	1.70	b	0.66	0.72	0.80
b2	2.90	3.00	3.10	c	0.23	0.30	0.35
D	6.30	6.50	6.70	E	6.70	7.00	7.30
E1	3.30	3.50	3.70	e	2.30 REF		
e1	4.60 REF			L	0.75	--	1.15
θ	0°	--	10°				